

# Excitation-Dependent Raman Modes of Ion-Induced Defects in Monolayer MoSe<sub>2</sub>

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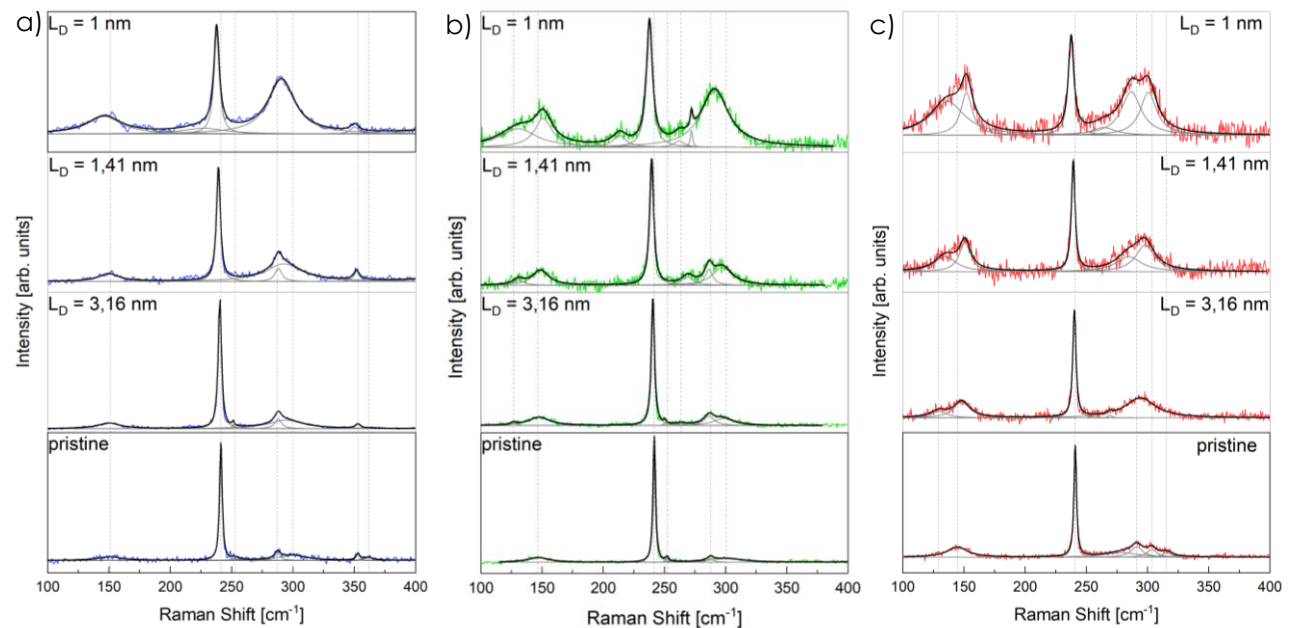
Transition metal dichalcogenide (TMDC) monolayers, such as MoSe<sub>2</sub>, have been extensively studied due to their unique physical properties. Intrinsic and induced defects can significantly influence their electronic and optical properties, impacting device performance and reliability. While defect studies are well-established for MoS<sub>2</sub> [1], research on defects in monolayers of MoSe<sub>2</sub> remains limited. Raman spectroscopy is a non-destructive and accessible technique for analyzing defects in 2D materials.

In this study, we induce point defects in a CVD-grown MoSe<sub>2</sub> monolayer via bombardment with singly charged argon ions with an energy of 600 eV. The ion fluences range from 10<sup>13</sup> ions·cm<sup>-2</sup> up to 10<sup>14</sup> ions·cm<sup>-2</sup>. The resulting defects are analyzed using Raman spectroscopy with three excitation energies, 2.71 eV, 2.33 eV and 1.95 eV. Additionally, cryogenic and room temperature measurements including Stokes and anti-Stokes modes were done. With increasing defect density, a shift in the A'<sub>1</sub> mode at 240 cm<sup>-1</sup> becomes apparent. Defect-induced Raman modes were observed for all excitation energies in the range of 200 cm<sup>-1</sup> to 350 cm<sup>-1</sup> (Fig. 1). Furthermore, low-frequency modes emerge in the range from 100 cm<sup>-1</sup> to 150 cm<sup>-1</sup> under excitation at 2.33 eV and 1.95 eV excitation. Our results provide new insights into defect dynamics in MoSe<sub>2</sub> and highlight the power of multi-excitation Raman spectroscopy for probing point defects.

## References

[1] Mignuzzi, S., et al., Phys. Rev. B, 91.19 (2015), 195411

## Figures



**Figure 1:** Raman spectra of MoSe<sub>2</sub> as a function of the inter-defect distance  $L_D$ . **a)** Spectra were obtained with 2.71 eV. **b)** Spectra were obtained with 2.33 eV. **c)** Spectra were obtained with 1.95 eV.